

In the Claims:

Please amend claims 1 and 4 as follows:

1. (Amended) A process for etching away a fixed thickness of silicon oxide in an integrated circuit structure on a semiconductor substrate in an etching chamber which comprises:

- A1
- a) exposing an oxide surface of said integrated circuit structure on said semiconductor substrate in said etching chamber to a nitrogen plasma; and
 - b) maintaining a bias on an electrode in said etching chamber during said exposure of said oxide surface to said nitrogen plasma to control the flow of components of said nitrogen plasma toward said substrate;

whereby a fixed thickness of silicon oxide will be removed from said oxide surface, with the oxide thickness removed dependent upon the power level of said bias on said electrode in said etching chamber.
